

Preliminary Constructions

Goda Kaisha IP Bridge 1 v. Broadcom Ltd., et al., Case. No. 2:16-cv-134

U.S. Patents No. 6,538,324, 6,197,696, RE41,980, 7,126,174, 8,354,726, and RE43,729

<u>Disputed Term</u>	<u>Preliminary Construction</u>
United States Patent No. 7,126,174	
A. "a trench isolation region surrounding an active area of a semiconductor substrate" ('174 Pat., Cl. 1)	Plain and ordinary meaning (Reject Defendants' proposal of "lateral boundary")
United States Patent No. 8,354,726	
C. "formed on the side surface of the [first/second] gate electrode" ('726 Pat., Cls. 1, 43)	"covering the side surface of the [first/second] gate electrode"
D. "a stress-containing insulating film containing internal stress and formed to cover the first gate electrode, the first side-wall insulating film, the auxiliary pattern, and the second side-wall insulating film" ('726 Pat., Cl. 1)	"a stress-containing insulating film containing internal stress and also covering the first gate electrode, the first side-wall insulating film, the auxiliary pattern, and the second side-wall insulating film"
E. "the first gate electrode is formed on the first active region through a gate insulating film including nitrogen" ('726 Pat., Cls. 20, 43, 54)	"the first gate electrode is formed on the first active region, with a nitrogen-containing gate insulating film between the first gate electrode and the first active region"
F. "an interlayer insulating film on the silicide layer through the stress-containing insulating film" ('726 Pat., Cls. 23, 57)	"an interlayer insulating film formed on the silicide layer, with the stress-containing insulating film being between the interlayer insulating film and the silicide layer"

United States Patent No. 6,197,696	
G. "using the [first resist pattern/second resist pattern and the mask pattern/patterned third insulating film] as a mask" ('696 Pat., Cl. 13)	"using the [first resist pattern/second resist pattern and the mask pattern/patterned third insulating film] to define areas for etching"
United States Patent No. 6,538,324	
H. Preambles of Claims 1 and 5 of the '324 Patent	The phrase "[a] barrier film preventing diffusion of copper from a copper wiring layer formed on a semiconductor substrate" in Claim 1 and the phrase "prevents diffusion of copper from a copper wiring layer formed on a semiconductor substrate" in Claim 5 are not limiting .
I. "film" ('324 Pat., Cls. 1, 5)	Plain and ordinary meaning
J. "said first film being composed of crystalline metal containing nitrogen therein" ('324 Pat., Cls. 1, 5)	"the first film is distinct from the second film, and the first film consists essentially of a mixture of crystalline or polycrystalline metal with nitrogen throughout" (Reject Defendants' proposal of "closed-ended")
K. "said second film being composed of amorphous metal nitride" ('324 Pat., Cls. 1, 5)	"the second film is distinct from the first film, and the second film consists essentially of amorphous metal nitride" (Reject Defendants' proposal of "closed-ended")
L. "[said barrier film being constituted of] common metal atomic species" ('324 Pat., Cls. 1, 5)	"the layers of the barrier film contain atoms of the same metal"
United States Patent No. RE41,980	
M. "a surface protecting film" ('980 Pat., Cls. 18, 35)	"a surface protecting film including distinct first and second dielectric films"
N. "interlayer insulating film" ('980 Pat., Cls. 18, 33, 35, 50)	"an insulating film located between but not within layers"

O. "small dielectric constant" ('980 Pat., Cls. 18, 35)	"a dielectric constant less than that of silicon dioxide"
P. "said bonding pad in said opening and said second dielectric film of said surface protecting film completely cover said first dielectric film so as not to expose said first dielectric film" ('980 Pat., Cl. 18)	"the bonding pad and the second dielectric film collectively cover the first dielectric film so that it is not exposed to above"
Q. "wherein said bonding pad covers said opening" ('980 Pat., Cl. 35)	Plain and ordinary meaning
United States Patent No. RE43,729	
R. "performed within one cycle" ('729 Pat., Cl. 21)	"performed within one clock cycle"